

### N-channel TrenchMOS standard level FET

Rev. 02 — 16 December 2010

**Product data sheet** 

#### 1. Product profile

#### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

#### 1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

#### **1.3 Applications**

DC-to-DC converters

General purpose switching

#### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	200	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}$	-	-	20	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	-	150	W
Static cha	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 10 \text{ A}; \\ T_{j} = 25 \text{ °C} \end{array}$	-	120	130	mΩ
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 20 A; V <sub>DS</sub> = 160 V; T <sub>j</sub> = 25 °C	-	22	-	nC

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#### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D mounting base; connected to drain	mbb076 S		
			SOT404 (D2PAK)	

[1] It is not possible to make a connection to pin 2.

#### 3. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PHB20NQ20T	D2PAK	plastic gle-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

### 4. Limiting values

#### Table 4. Limiting values

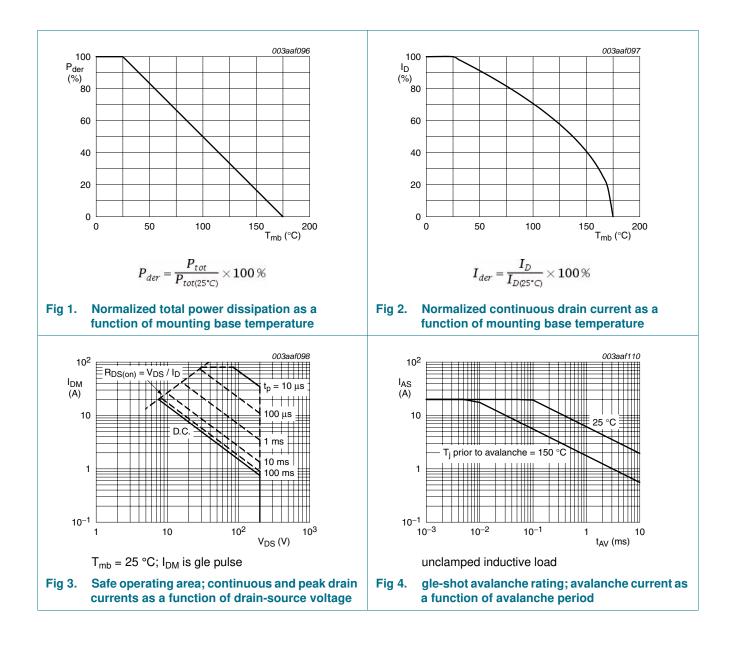
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	200	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	200	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}$	-	14	А
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}$	-	20	А
I <sub>DM</sub>	peak drain current	pulsed; T <sub>mb</sub> = 25 °C	-	80	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	150	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	20	А
I <sub>SM</sub>	peak source current	pulsed; T <sub>mb</sub> = 25 °C	-	80	А
Avalanche rug	ggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy		-	252	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$\label{eq:V_sup} \begin{array}{l} V_{sup} \leq 25 \ \text{V}; \ \text{V}_{GS} = 10 \ \text{V}; \ \text{T}_{j(\text{init})} = 25 \ ^{\circ}\text{C}; \\ \text{R}_{GS} = 50 \ \Omega; \ \text{unclamped} \end{array}$	-	20	Α
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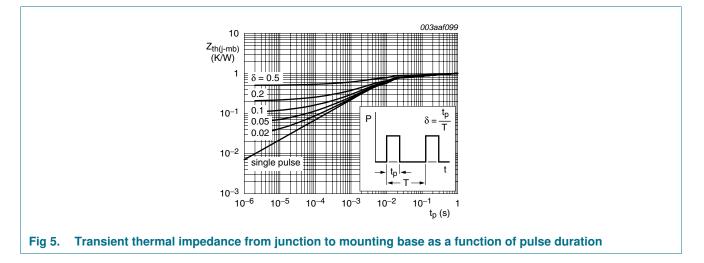
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#### N-channel TrenchMOS standard level FET

#### **Thermal characteristics** 5.

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Table 5.	I nermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	1	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	mounted on printed-circuit board ; minimum footprint	-	50	-	K/W



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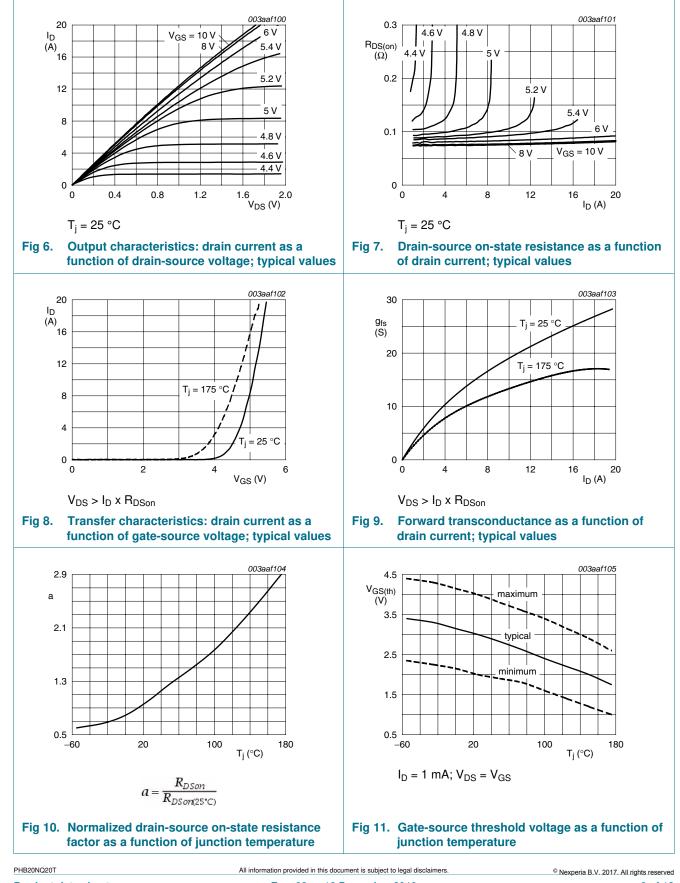
#### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub> drain-source breakdown		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	178	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	200	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
		$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	0.02	100	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	0.02	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 175 °C	-	-	377	mΩ
	resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C	-	120	130	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 20 \text{ A}; V_{DS} = 160 \text{ V}; V_{GS} = 10 \text{ V};$	-	65	-	nC
Q <sub>GS</sub>	gate-source charge	$T_j = 25 \ ^{\circ}C$	-	10	-	nC
Q <sub>GD</sub>	gate-drain charge		-	22	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2470	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \ ^{\circ}C$	-	207	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	90	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 100 \text{ V};  \text{R}_{L} = 4.7  \Omega;  \text{V}_{GS} = 10 \text{ V}; \label{eq:VDS}$	-	15	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5.6 \ \Omega; \ T_j = 25 \ ^{\circ}C$	-	46	-	ns
d(off)	turn-off delay time		-	50	-	ns
f	fall time		-	38	-	ns
L <sub>D</sub>	internal drain inductance	measured from tab to centre of die ; $T_{j}=25\ ^{\circ}\text{C}$	-	3.5	-	nH
Ls	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V <sub>SD</sub>	source-drain voltage	$I_{S} = 20 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	0.95	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{\rm S} = 20 \text{ A}; \text{ dI}_{\rm S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	124	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS}$ = -10 V; $V_{DS}$ = 25 V; $T_j$ = 25 °C	-	0.74	-	μC

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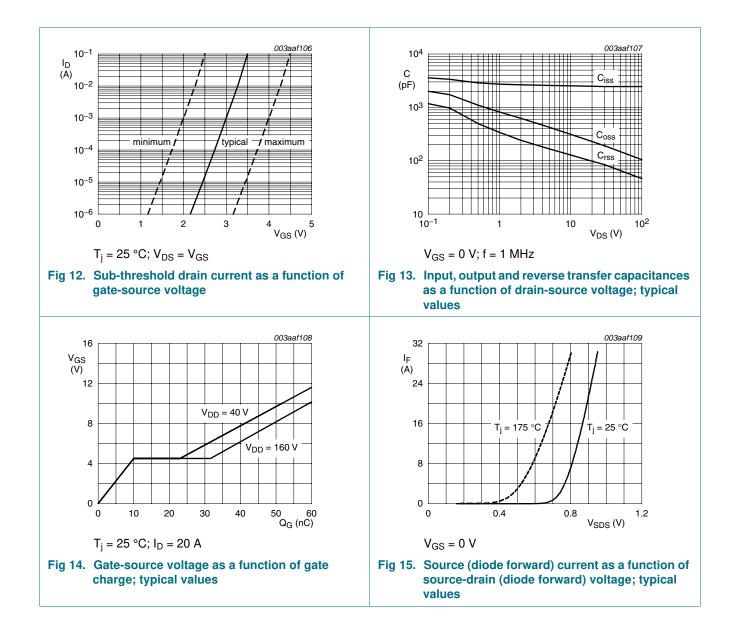
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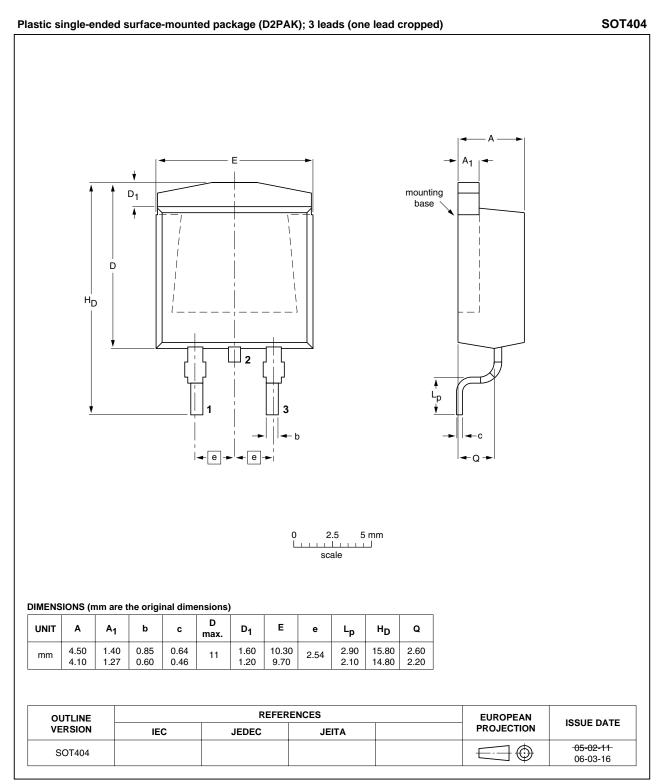
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#### 7. Package outline



#### Fig 16. Package outline SOT404 (D2PAK)

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### 8. Revision history

Table 7. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PHB20NQ20T v.2	20101216	Product data sheet	-	PHB_PHP20NQ20T v.1
Modifications:	guidelines of • Legal texts	of this data sheet has b of NXP Semiconductors. have been adapted to th er PHB20NQ20T separa	ne new company name	
PHB_PHP20NQ20T v.1	19990801	Product specification	-	-

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#### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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#### N-channel TrenchMOS standard level FET

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#### N-channel TrenchMOS standard level FET

#### 11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values2
5	Thermal characteristics4
6	Characteristics5
7	Package outline8
8	Revision history9
9	Legal information10
9.1	Data sheet status10
9.2	Definitions10
9.3	Disclaimers
9.4	Trademarks11
10	Contact information11